



LIGITEK

NPN SILICON PHOTOTRANSISTOR LED LAMPS	LPT3323	SERIES
Package Dimension	Features	
	<ul style="list-style-type: none"> . High illumination sensitivity . Stable characteristics . Spectrally and mechanically matched with IR emitter 	
<p>1.EMITTER 2.COLLECTOR</p>	Description	
<p>The LPT3323 series are silicon nitride passivated NPN planar phototransistors with exceptionally stable characteristics and high illumination sensitivity the cases of LPT3323 are encapsulated in water clear plastic T1 3/4 package individualt</p>		
<p>Note:1.All dimension are in millimeter tolerance is $\pm 0.25\text{mm}$ unless otherwise noted 2.Specifications are subject to change without notice</p>		

MAXIMUM RATINGS(Ta=25)		
PARAMETER	MAXIMUM RATINGS	UNIT
Power Dissipation	100	mw
Collector-Emitter Voltage	30	V
Emitter-Collector Voltage	5	V
Operating Temperature	-50 TO +100	
Storage Temperature	-50 TO +100	
Lead Soldering Temperature(1.6mm From Body)	260 for 5 seconds	

ELECTRICAL CHARACTERISTICS(Ta=25)						
PARAMETER	SYMBOL	Min.	Typ.	Max.	UNIT	TEST CONDITION
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_c=1\text{mA}$ $E_e=0\text{mw/cm}^2$
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5			V	$I_E=100 \mu\text{A}$ $E_e=0\text{mw/cm}^2$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.4	V	$I_c=0.5\text{mA}$ $E_e=20\text{mw/cm}^2$
Rise Time	T_r		5		μs	$V_{CE}=30\text{V}$ $I_C=800 \mu\text{A}, R_L=1\text{K}$
Fall Time	T_f		5		μs	
Collector Dark Current	I_{CEO}			100	nA	$V_{CE}=10\text{V}$ $E_e=0\text{mw/cm}^2$
On State Collector Current	$I_p(on)$	1		2	mA	$V_{CE}=5\text{v}$ $E_e=1\text{mw/cm}^2$ $P=940\text{nm}$
		2		4	mA	
		4		8	mA	
		8			mA	